MPSW92

One Watt High Voltage Transistor

PNP Silicon

ON Semiconductor®

http://onsemi.com

Features

- Pb−Free Packages are Available*

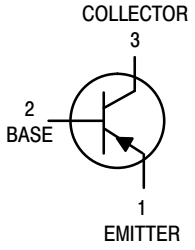
MAXIMUM RATINGS

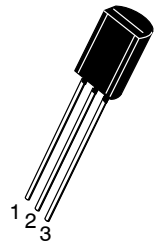
Rating	Symbol	Value	Unit
Collector − Emitter Voltage	V_{CEO}	−300	Vdc
Collector − Base Voltage	V_{CBO}	−300	Vdc
Emitter − Base Voltage	V_{EBO}	−5.0	Vdc
Collector Current − Continuous	I_C	−500	mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	1.0 8.0	W mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	2.5 20	W mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

THERMAL CHARACTERISTICS

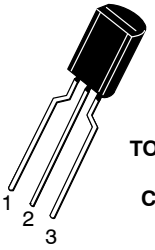
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction−to−Ambient	$R_{\theta JA}$	125	°C/W
Thermal Resistance, Junction to Case	$R_{\theta JC}$	50	°C/W

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.





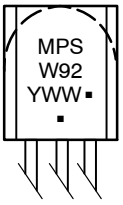
STRAIGHT LEAD
BULK PACK



BENT LEAD
TAPE & REEL
AMMO PACK

TO−92 1 WATT
(TO−226)
CASE 29−10
STYLE 1

MARKING DIAGRAM



MPSW45x = Device Code
x = 45A Devices
A = Assembly Location
Y = Year
WW = Work Week
▪ = Pb−Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector−Emitter Breakdown Voltage (Note 1) (I_C = −1.0 mAdc, I_B = 0)	$V_{(BR)CEO}$	−300	−	Vdc
Collector−Base Breakdown Voltage (I_C = −100 μAdc, I_E = 0)	$V_{(BR)CBO}$	−300	−	Vdc
Emitter−Base Breakdown Voltage (I_E = −100 μAdc, I_C = 0)	$V_{(BR)EBO}$	−5.0	−	Vdc
Collector Cutoff Current (V_{CB} = −200 Vdc, I_E = 0)	I_{CBO}	−	−0.25	μAdc
Emitter Cutoff Current (V_{EB} = −3.0 Vdc, I_C = 0)	I_{EBO}	−	−0.1	μAdc
ON CHARACTERISTICS (Note 1)				
DC Current Gain (I_C = −1.0 mAdc, V_{CE} = −10 Vdc) (I_C = −10 mAdc, V_{CE} = −10 Vdc) (I_C = −30 mAdc, V_{CE} = −10 Vdc)	h_{FE}	 25 40 25	 − − −	−
Collector−Emitter Saturation Voltage (I_C = −20 mAdc, I_B = −2.0 mAdc)	$V_{CE(sat)}$	−	−0.5	Vdc
Base−Emitter Saturation Voltage (I_C = −20 mAdc, I_B = −2.0 mAdc)	$V_{BE(sat)}$	−	−0.9	Vdc
SMALL−SIGNAL CHARACTERISTICS				
Current−Gain − Bandwidth Product (I_C = −10 mAdc, V_{CE} = −20 Vdc, f = 20 MHz)	f_T	50	−	MHz
Collector−Base Capacitance (V_{CB} = −20 Vdc, I_E = 0, f = 1.0 MHz)	C_{cb}	−	6.0	pF

1. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

ORDERING INFORMATION

Device	Package	Shipping†
MPSW92	TO−92	5000 Units / Box
MPSW92G	TO−92 (Pb−Free)	5000 Units / Box
MPSW92RLREG	TO−92 (Pb−Free)	2000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

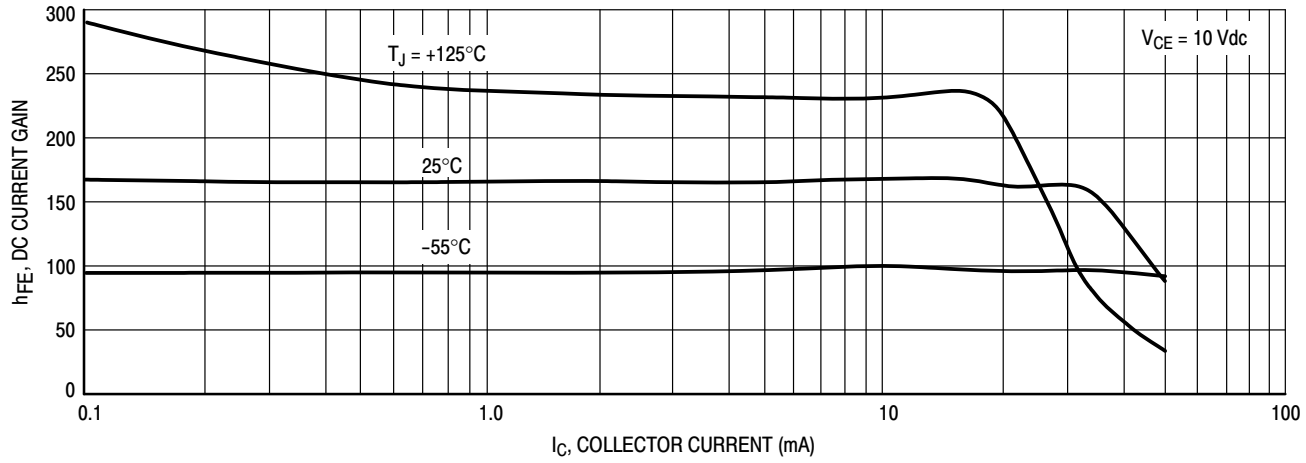


Figure 1. DC Current Gain

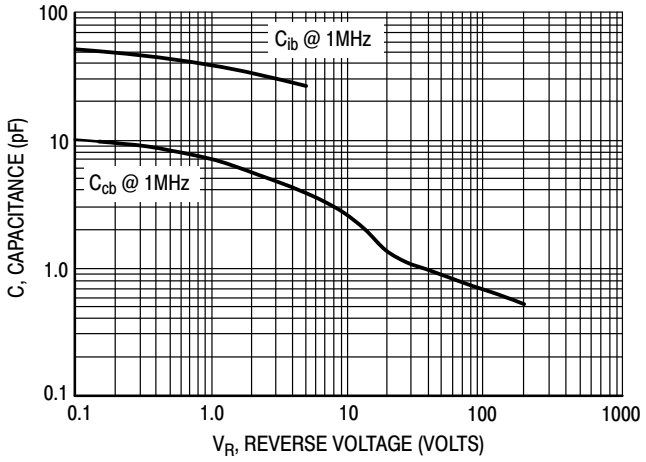


Figure 2. Capacitance

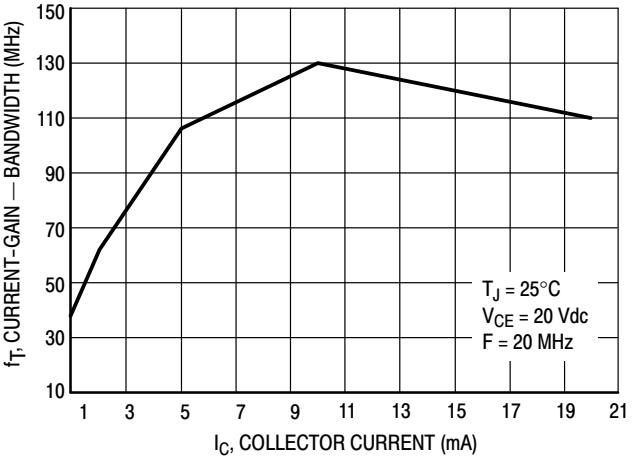


Figure 3. Current−Gain − Bandwidth

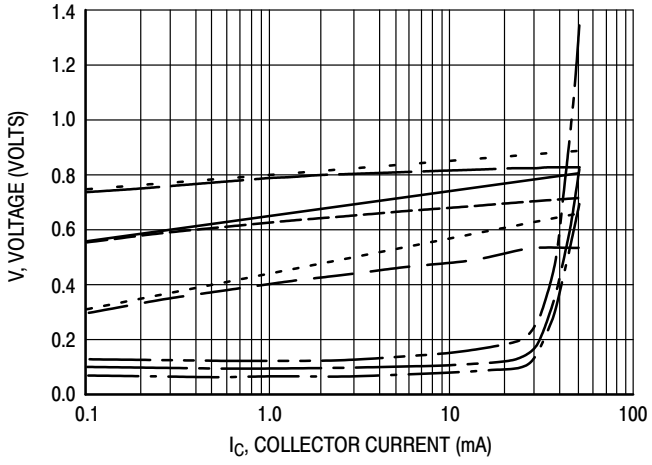
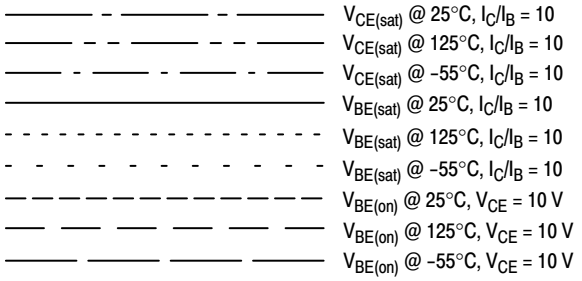


Figure 4. "ON" Voltages



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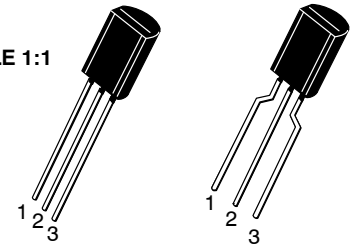
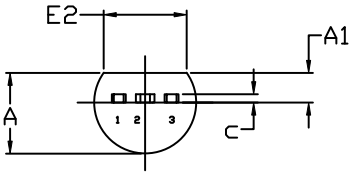
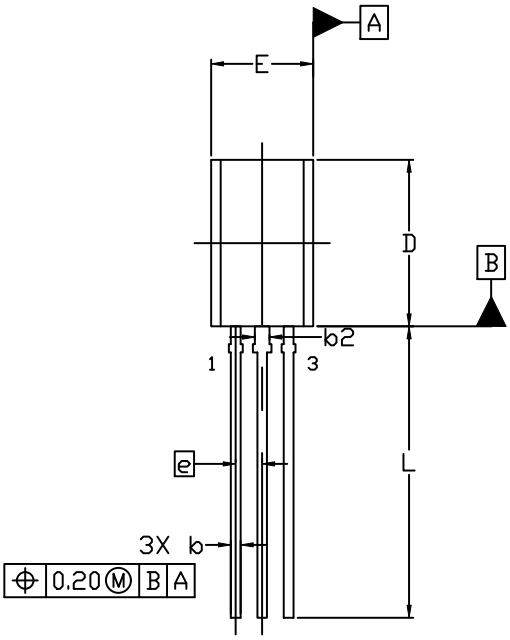
SCALE 1:1



STRAIGHT LEAD



END VIEW



TOP VIEW

NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR GATE PROTRUSIONS.
4. DIMENSION b AND b2 DOES NOT INCLUDE DAMBAR PROTRUSION. LEAD WIDTH INCLUDING PROTRUSION SHALL NOT EXCEED 0.20. DIMENSION b2 LOCATED ABOVE THE DAMBAR PORTION OF MIDDLE LEAD.

	MILLIMETERS		
DIM	MIN.	NOM.	MAX.
A	3.75	3.90	4.05
A1	1.28	1.43	1.58
b	0.38	0.465	0.55
b2	0.62	0.70	0.78
c	0.35	0.40	0.45
D	7.85	8.00	8.15
E	4.75	4.90	5.05
E2	3.90	---	---
e	1.27 BSC		
L	13.80	14.00	14.20

STYLES AND MARKING ON PAGE 3

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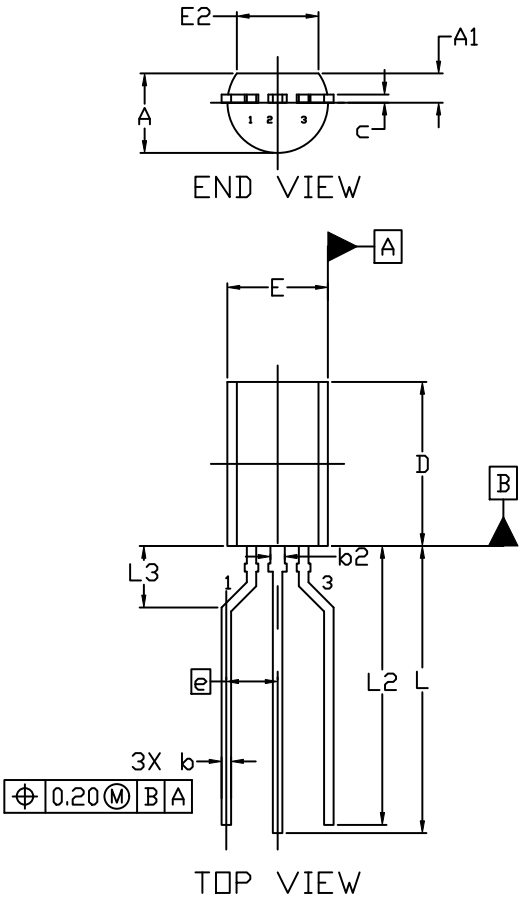
FORMED LEAD



NOTES:
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	MILLIMETERS		
DIM	MIN.	NOM.	MAX.
A	3.75	3.90	4.05
A1	1.28	1.43	1.58
b	0.38	0.465	0.55
b2	0.62	0.70	0.78
c	0.35	0.40	0.45
D	7.85	8.00	8.15
E	4.75	4.90	5.05
E2	3.90	---	---
e	2.50 BSC		
L	13.80	14.00	14.20
L2	13.20	13.60	14.00
L3	3.00 REF		

STYLES AND MARKING ON PAGE 3

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STYLE 1:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

STYLE 2:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 3:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 4:
PIN 1. CATHODE
2. CATHODE
3. ANODE

STYLE 5:
PIN 1. DRAIN
2. SOURCE
3. GATE

STYLE 6:
PIN 1. GATE
2. SOURCE & SUBSTRATE
3. DRAIN

STYLE 7:
PIN 1. SOURCE
2. DRAIN
3. GATE

STYLE 8:
PIN 1. DRAIN
2. GATE
3. SOURCE & SUBSTRATE

STYLE 9:
PIN 1. BASE 1
2. EMITTER
3. BASE 2

STYLE 10:
PIN 1. CATHODE
2. GATE
3. ANODE

STYLE 11:
PIN 1. ANODE
2. CATHODE & ANODE
3. CATHODE

STYLE 12:
PIN 1. MAIN TERMINAL 1
2. GATE
3. MAIN TERMINAL 2

STYLE 13:
PIN 1. ANODE 1
2. GATE
3. CATHODE 2

STYLE 14:
PIN 1. EMITTER
2. COLLECTOR
3. BASE

STYLE 15:
PIN 1. ANODE 1
2. CATHODE
3. ANODE 2

STYLE 16:
PIN 1. ANODE
2. GATE
3. CATHODE

STYLE 17:
PIN 1. COLLECTOR
2. BASE
3. EMITTER

STYLE 18:
PIN 1. ANODE
2. CATHODE
3. NOT CONNECTED

STYLE 19:
PIN 1. GATE
2. ANODE
3. CATHODE

STYLE 20:
PIN 1. NOT CONNECTED
2. CATHODE
3. ANODE

STYLE 21:
PIN 1. COLLECTOR
2. EMITTER
3. BASE

STYLE 22:
PIN 1. SOURCE
2. GATE
3. DRAIN

STYLE 23:
PIN 1. GATE
2. SOURCE
3. DRAIN

STYLE 24:
PIN 1. EMITTER
2. COLLECTOR/ANODE
3. CATHODE

STYLE 25:
PIN 1. MT 1
2. GATE
3. MT 2

STYLE 26:
PIN 1. V_{CC}
2. GROUND 2
3. OUTPUT

STYLE 27:
PIN 1. MT
2. SUBSTRATE
3. MT

STYLE 28:
PIN 1. CATHODE
2. ANODE
3. GATE

STYLE 29:
PIN 1. NOT CONNECTED
2. ANODE
3. CATHODE

STYLE 30:
PIN 1. DRAIN
2. GATE
3. SOURCE

STYLE 31:
PIN 1. GATE
2. DRAIN
3. SOURCE

STYLE 32:
PIN 1. BASE
2. COLLECTOR
3. EMITTER

STYLE 33:
PIN 1. RETURN
2. INPUT
3. OUTPUT

STYLE 34:
PIN 1. INPUT
2. GROUND
3. LOGIC

STYLE 35:
PIN 1. GATE
2. COLLECTOR
3. EMITTER

GENERIC MARKING DIAGRAM*

XXXX = Specific Device Code
A = Assembly Location
L = Wafer Lot
Y = Year
W = Work Week
▪ = Pb−Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.

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DESCRIPTION:	**TO−92 (TO−226) 1 WATT**		**PAGE 3 OF 3**

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